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[Diodes Incorporated](#)
[DMN2100UDM-7](#)

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DMN2100UDM

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = 25°C
20V	55mΩ @ V _{GS} = 4.5V	4.0A
	70mΩ @ V _{GS} = 2.5V	3.5A
	90mΩ @ V _{GS} = 1.8V	3.1A
	130mΩ @ V _{GS} = 1.5V	2.5A

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

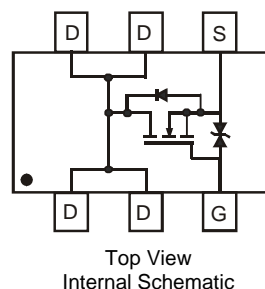
Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance (R_{DS(on)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions

Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.015 grams (approximate)

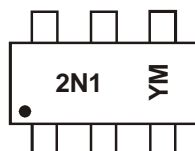


Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2100UDM-7	SOT26	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



2N1 = Marking Code
 YM = Date Code Marking
 Y = Year (ex: U = 2007)
 M = Month (ex: 9 = September)

Date Code Key

Year	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017	
Code	U	V	W	X	Y	Z	A	B	C	D	E	
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V_{DSS}	20	V	
Gate-Source Voltage	V_{GSS}	± 8	V	
Continuous Drain Current (Note 6) $V_{GS} = 4.5\text{V}$	Steady State	$T_A = 25^\circ\text{C}$	4.0	A
		$T_A = 70^\circ\text{C}$	3.1	A
	t<10s	$T_A = 25^\circ\text{C}$	4.5	A
		$T_A = 70^\circ\text{C}$	3.5	A
Pulsed Drain Current (10 μs pulse, duty cycle = 1%)	I_{DM}	13	A	
Maximum Body Diode Continuous Current	I_S	1.5	A	

Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)	P_D	$T_A = 25^\circ\text{C}$	1	W
		$T_A = 70^\circ\text{C}$	0.6	
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	Steady state	127	$^\circ\text{C/W}$
		t<10s	91	
Total Power Dissipation (Note 6)	P_D	$T_A = 25^\circ\text{C}$	1.5	W
		$T_A = 70^\circ\text{C}$	0.9	
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	Steady state	85	$^\circ\text{C/W}$
		t<10s	63	
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	3.1	$^\circ\text{C}$	
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$	

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 1	μA	$V_{GS} = \pm 8\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	0.6	—	1.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	32	55	m Ω	$V_{GS} = 4.5\text{V}, I_D = 6\text{A}$
		—	43	70		$V_{GS} = 2.5\text{V}, I_D = 4.0\text{A}$
		—	56	90		$V_{GS} = 1.8\text{V}, I_D = 1.5\text{A}$
		—	80	130		$V_{GS} = 1.5\text{V}, I_D = 1.0\text{A}$
Forward Transfer Admittance	$ Y_{fs} $	—	8	—	S	$V_{DS} = 10\text{V}, I_D = 6\text{A}$
Diode Forward Voltage	V_{SD}	—	0.7	1.1	V	$V_{GS} = 0\text{V}, I_S = 2\text{A}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	555	—	pF	$V_{DS} = 10\text{V}, V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	112	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	84	—	pF	
Total Gate Charge	Q_g	—	8.8	—	nC	$V_{DS} = 10\text{V}, V_{GS} = 4.5\text{V},$ $I_D = 6.5\text{A}$
Gate-Source Charge	Q_{gs}	—	1.4	—	nC	
Gate-Drain Charge	Q_{gd}	—	3	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	53	—	ns	$V_{DS} = 10\text{V}, I_D = 1.0\text{A}$ $V_{GS} = 4.5\text{V}, R_G = 6\Omega$
Turn-On Rise Time	t_r	—	78	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	561	—	ns	
Turn-Off Fall Time	t_f	—	234	—	ns	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate
 - Short duration pulse test used to minimize self-heating effect
 - Guaranteed by design. Not subject to production testing



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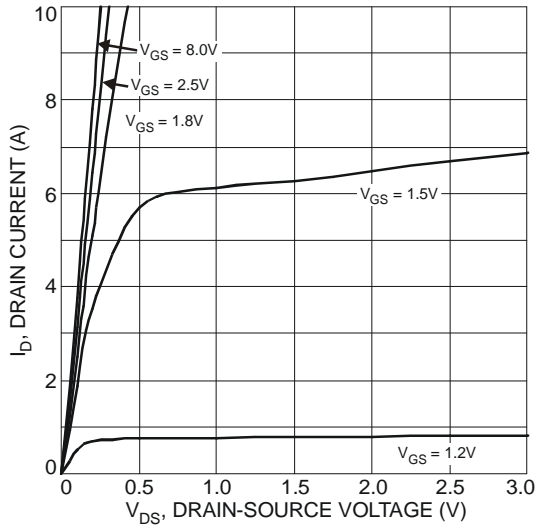


Fig. 1 Typical Output Characteristic

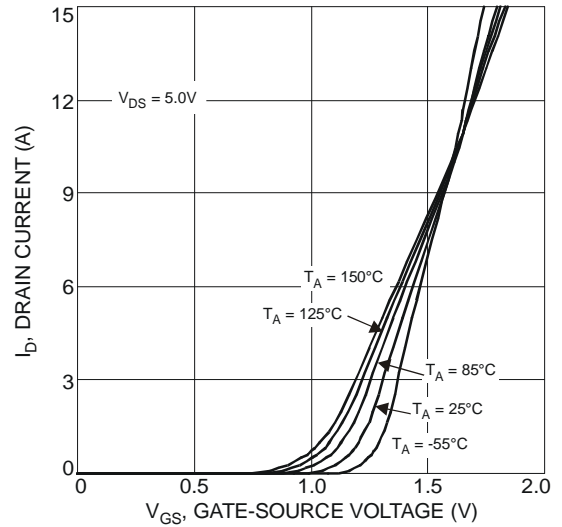


Fig. 2 Typical Transfer Characteristics

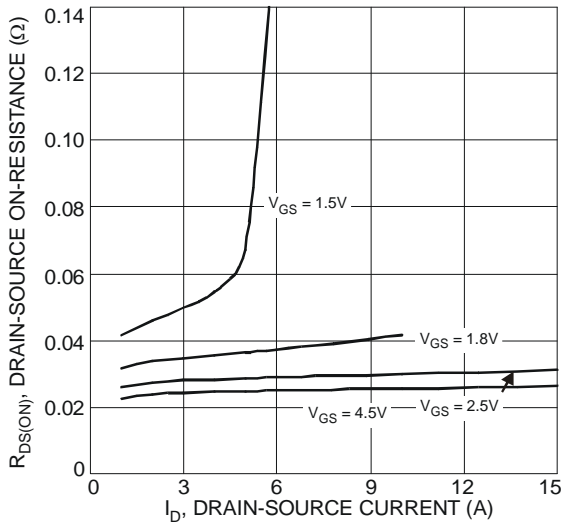


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

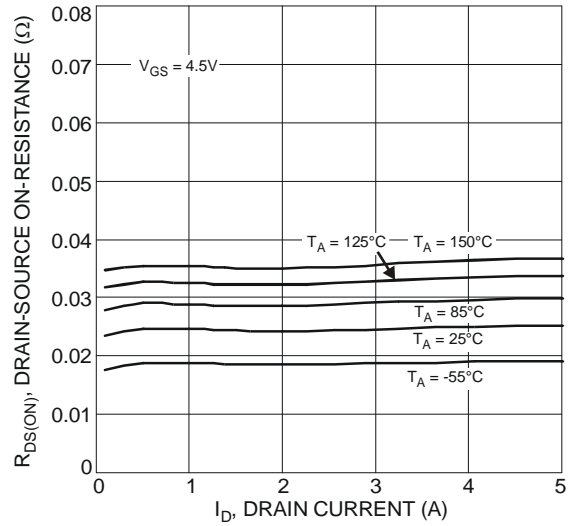


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

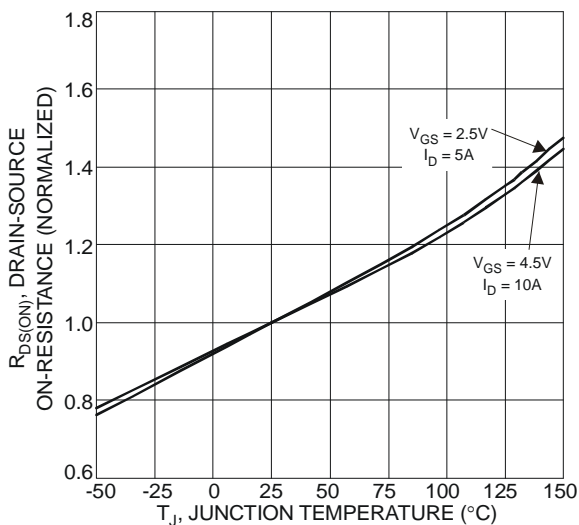


Fig. 5 On-Resistance Variation with Temperature

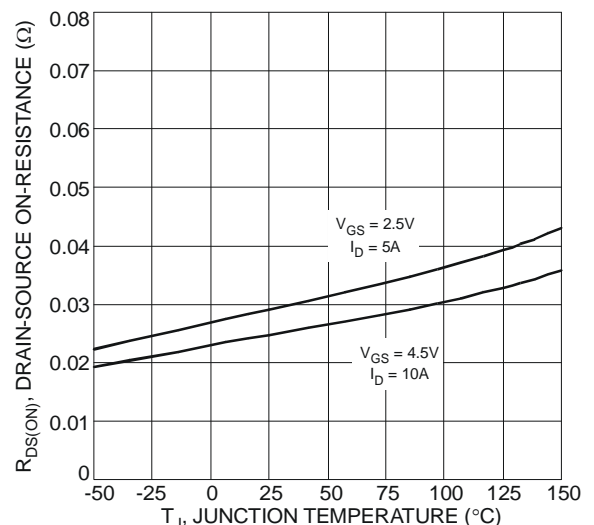


Fig. 6 On-Resistance Variation with Temperature



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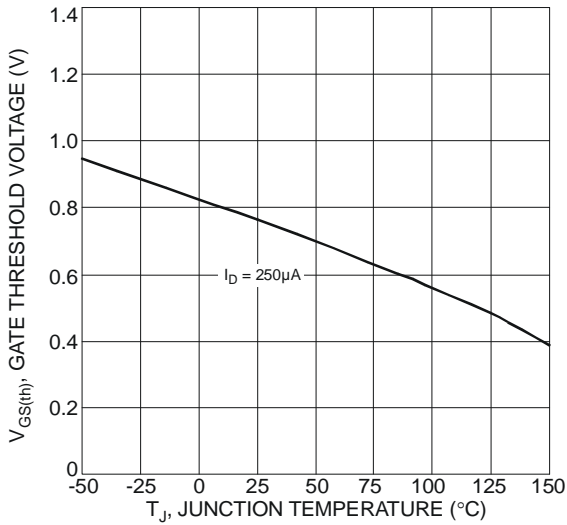


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

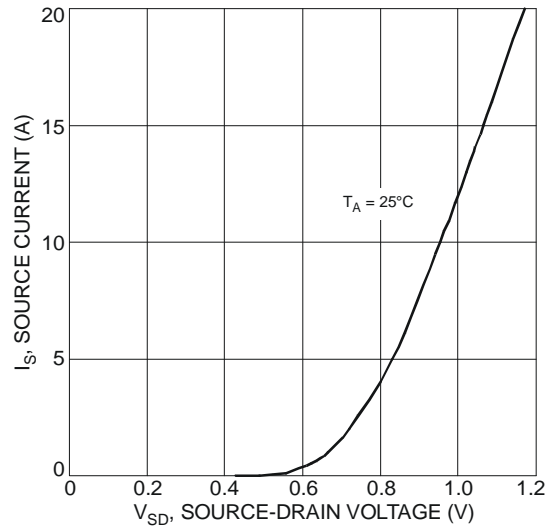


Fig. 8 Diode Forward Voltage vs. Current

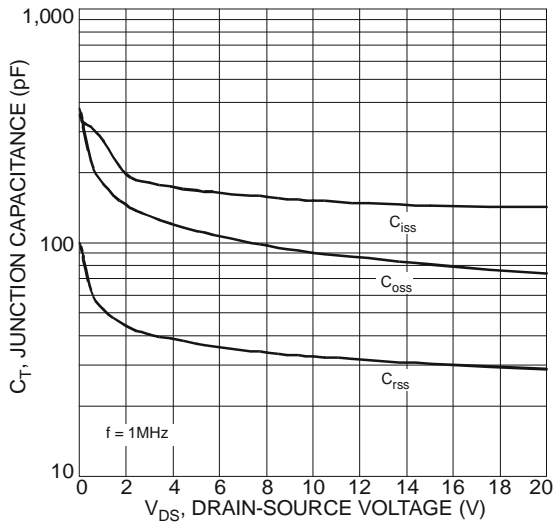


Fig. 9 Typical Junction Capacitance

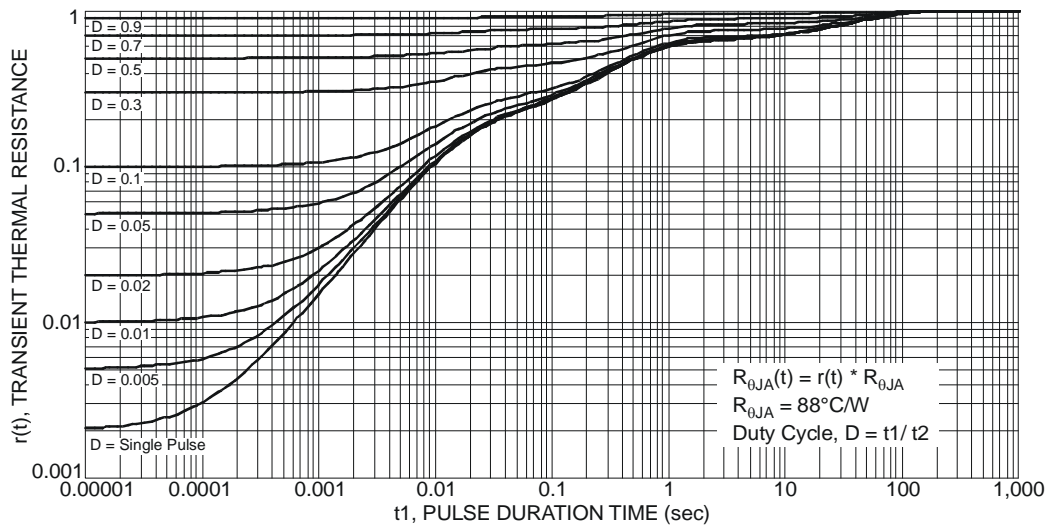
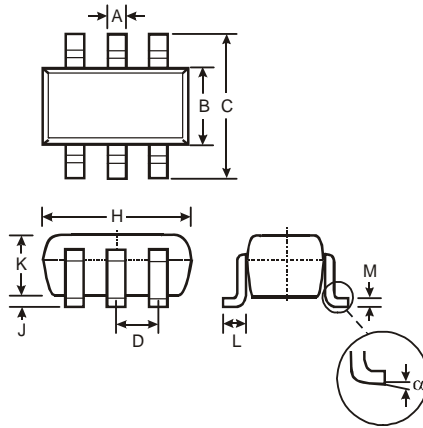


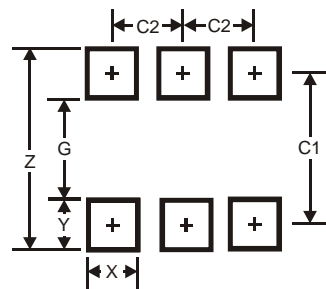
Fig. 10 Transient Thermal Resistance

Package Outline Dimensions



SOT26			
Dim	Min	Max	Typ
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	—	—	0.95
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
α	0°	8°	—
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
X	0.55
Y	0.80
C1	2.40
C2	0.95

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